

Description

The PDCSD12C is a 12V bi-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data and power line. The PDCSD12C-T complies with the IEC 61000-4-2 (ESD) standard with ±30 kV air and ±30 kV contact discharge. It is assembled into an ultra-small lead-free SOD-323 package. The small size and high ESD surge protection make PDCSD12C-T an ideal choice to protect cell phone, digital cameras, audio players and many other portable applications.

Features

- 375W peak pulse power (8 /20µs)
- Protects one data or power line
- Ultra low leakage: nA level
- Operating voltage: 12V
- Low clamping voltage
- 2-pin leadless package
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test Air

discharge: ±30kV

Contact discharge: ±30kV

- IEC61000-4-5 (Lightning) 15A (8/20µs)
- RoHS Compliant

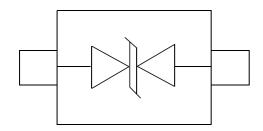
Mechanical Characteristics

- Package: SOD-323
- Case Material: "Green" Molding Compound.
 Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Below

Applications

- Cellular Handsets and Accessories
- Personal Digital Assistants
- Notebooks and Handhelds
- Portable Instrumentation
- Digital Cameras
- Peripherals
- Audio Players

Dimensions and Pin Configuration



Circuit and Pin Schematic

Marking Information

12

12 = Device Marking Code

Ordering Information

Part Number	Marking	Packaging	Reel Size
PDCSD12C	12	10000/Tape & Reel	7 inch

www.pdwsemi.com



Absolute Maximum Ratings (TA=25°C unless otherwise specified)

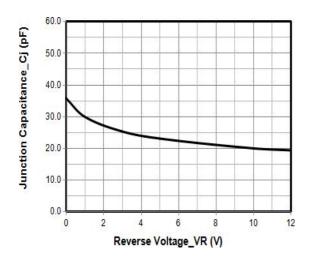
Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20µs)	Ppk	375	W
Peak Pulse Current (8/20µs)	Ірр	15	А
ESD per IEC 61000-4-2 (Air)		±30	
ESD per IEC 61000-4-2 (Contact)	VESD	±30	kV
Operating Temperature Range	TJ	−55 to +125	°C
Storage Temperature Range	Tstg	−55 to +150	°C

Electrical Characteristics (TA=25°C unless otherwise specified)

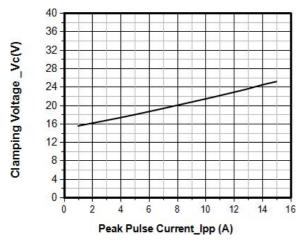
Parameter	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			12	V	
Breakdown Voltage	VBR	13.3			V	IT = 1mA
Reverse Leakage Current	I _R			0. 5	μA	VRWM = 12V
Clamping Voltage	Vc			16	V	IPP = 1A (8 x 20μs pulse)
Clamping Voltage	Vc			25	V	IPP = 15A (8 x 20µs pulse)
Junction Capacitance	Cı		35		pF	VR = 0V, f = 1MHz



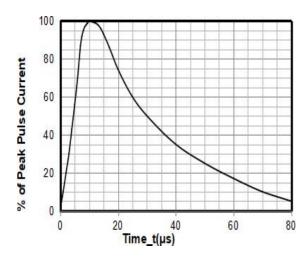
Typical Performance Characteristics (TA=25°C unless otherwise Specified)



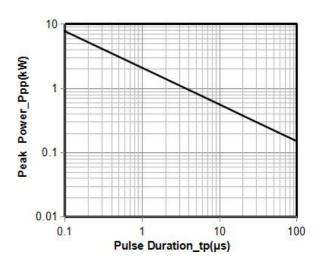
Junction Capacitance vs. Reverse Voltage



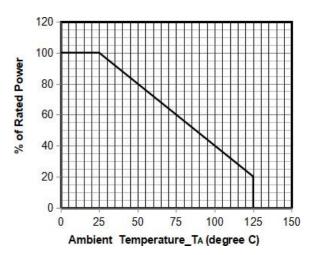
Clamping Voltage vs. Peak Pulse Current



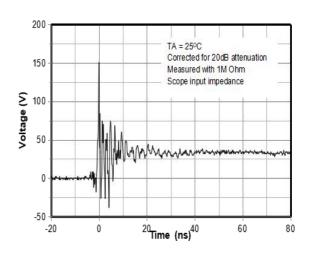
8 X 20µs Pulse Waveform



Peak Pulse Power vs. Pulse Time



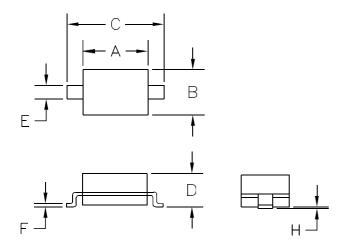
Power Derating Curve



ESD Clamping Voltage 8 kV Contact per IEC61000-4-2

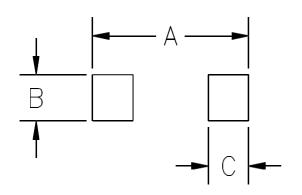


SOD-323 Package Outline Drawing



	DIMENSIO			
SYM	MILLIMETERS		INC	HES
	MIN	MAX	MIN	MAX
Α	1.50	1.80	0.060	0.071
В	1.20	1.40	0.045	0.054
С	2.30	2.70	0.090	0.107
D	1	1.10	-	0.043
Е	0.30	0.40	0.012	0.016
F	0.10	0.25	0.004	0.010
Н	-	0.10	-	0.004

Suggested Land Pattern



SYM	DIMENSIONS				
3 T IVI	MILLIMETERS	INCHES			
Α	3.15	0.120			
В	0.80	0.031			
С	0.80	0.031			